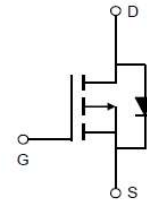


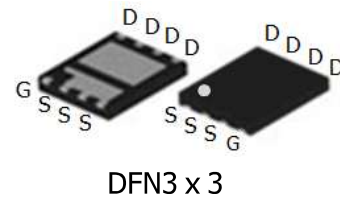
Feature

- -100V,-18A
 $R_{DS(ON)} < 95m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 110m\Omega @ V_{GS} = -4.5V$
- Advanced Trench Technology
- Lead free product is acquired
- Low Gate Charge
- Excellent Cdv/dt effect decline



Application

- PWM applications
- Load Switch
- Power management



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
18P10Q	AP18P10Q	PDFN3X3-8L	13 inch	-	5000

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a = 25^\circ\text{C}$)	I_D	-18	A
Continuous Drain Current ($T_a = 100^\circ\text{C}$)	I_D	-14.5	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-75	A
Singel Pulsed Avalanche Energy ⁽²⁾	E_{AS}	148	mJ
Power Dissipation	P_D	48	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	2.6	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-100	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -100V, V_{GS} = 0V$	-	-	-50	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	-1.2	-1.7	-2.5	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -10A$	-	78	95	m Ω
		$V_{GS} = -4.5V, I_D = -8A$	-	86	110	
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -20V, V_{GS} = 0V, f = 1MHz$	-	3029	-	pF
Output Capacitance	C_{oss}		-	129	-	
Reverse Transfer Capacitance	C_{rss}		-	76	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -50V, I_D = -10A,$ $V_{GS} = -10V, R_G = 3.3\Omega$	-	12	-	ns
Turn-on rise time	t_r		-	27.4	-	
Turn-off delay time	$t_{d(off)}$		-	79	-	
Turn-off fall time	t_f		-	53.6	-	
Total Gate Charge	Q_g	$V_{DS} = -50V, I_D = -18A,$ $V_{GS} = -10V$	-	44.5	-	nC
Gate-Source Charge	Q_{gs}		-	9	-	
Gate-Drain Charge	Q_{gd}		-	6	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$V_{GS} = 0V, I_S = 1A$	-	-	-1.2	V
Diode Forward current ⁽⁴⁾	I_S		-	-	-18	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^{\circ}\text{C}, V_{DD} = -25V, R_G = 25\Omega, L = 1mH, I_{AS} = 17.2A$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10$ sec

Typical Characteristics

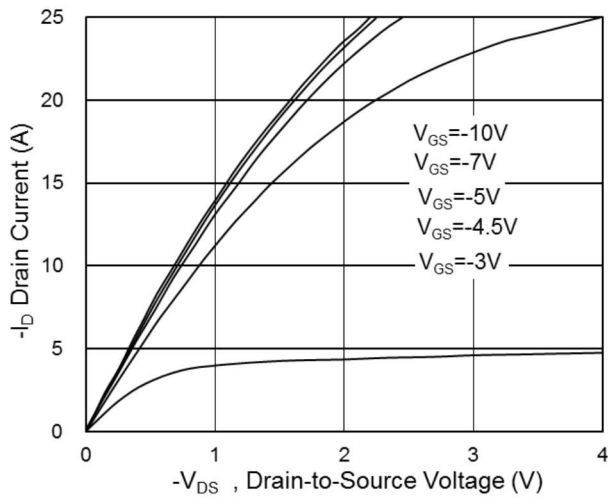


Fig.1 Typical Output Characteristics

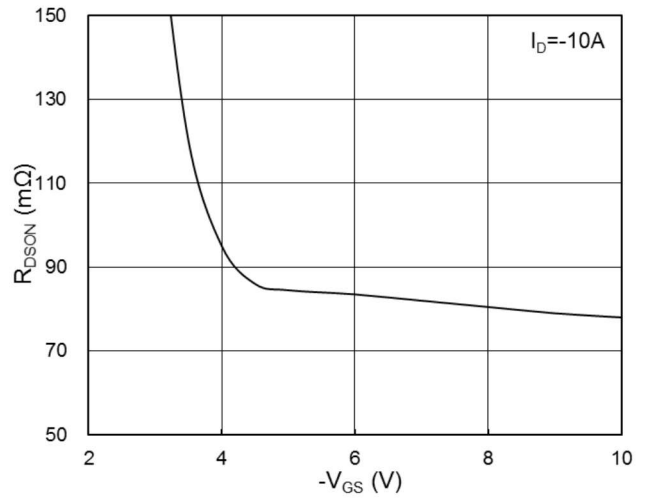


Fig.2 On-Resistance vs. G-S Voltage

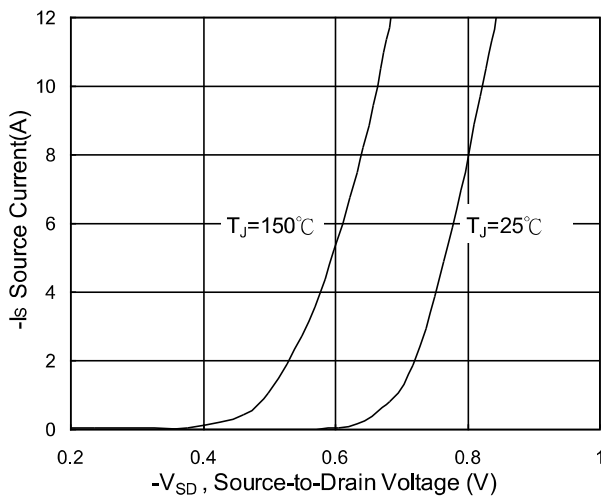


Fig.3 Typical S-D Diode Forward Voltage

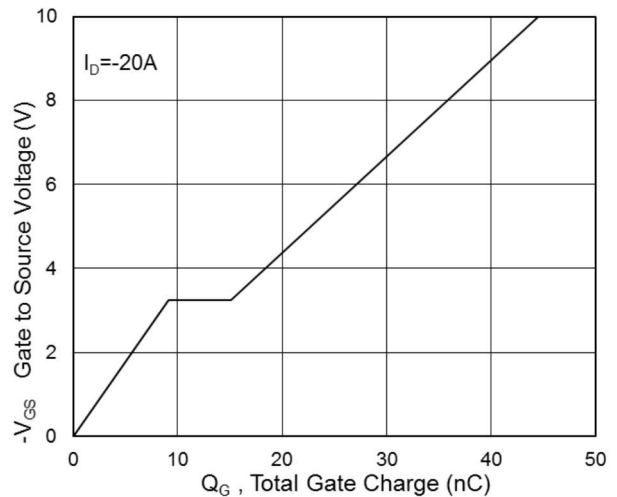


Fig.4 Gate-Charge Characteristics

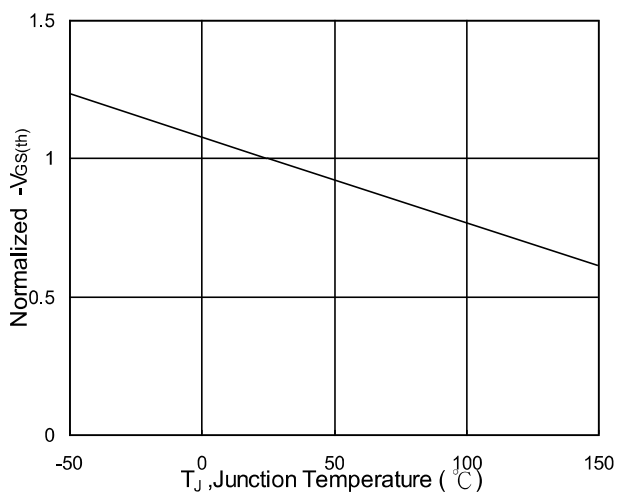


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

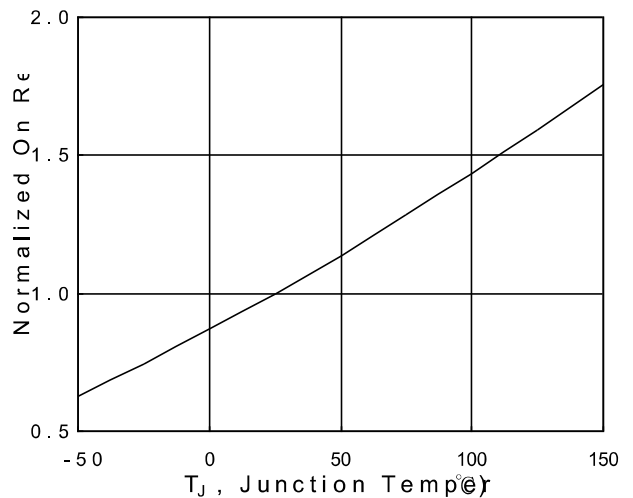


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

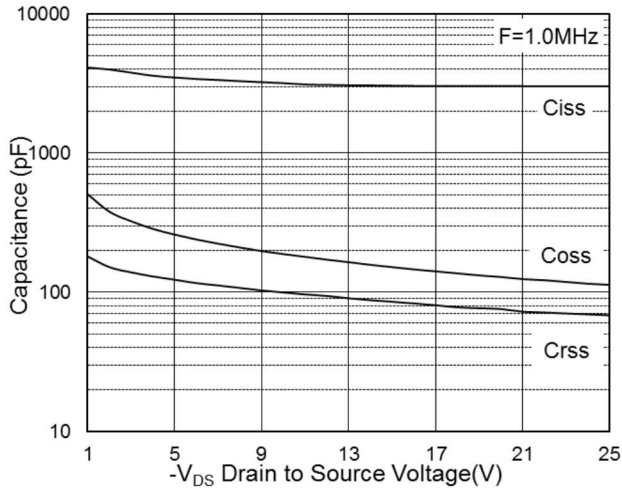


Fig.7 Capacitance

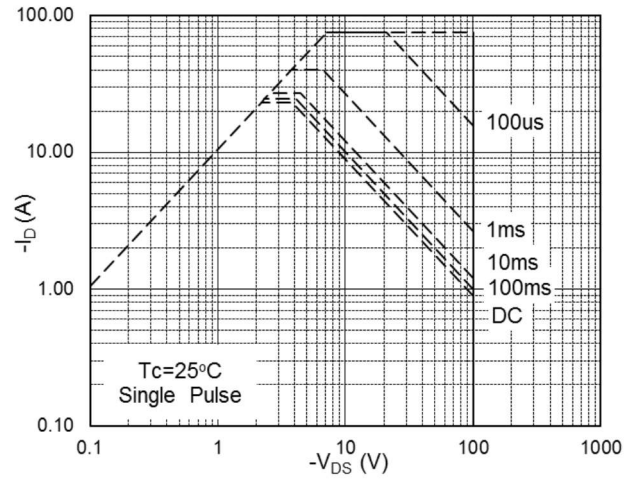


Fig.8 Safe Operating Area

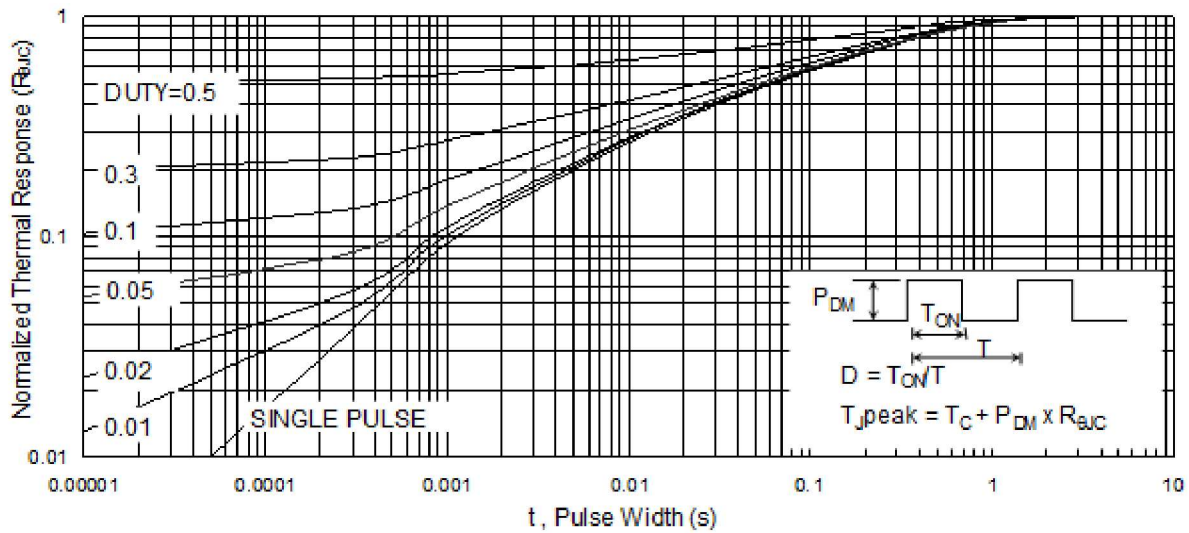


Fig.9 Normalized Maximum Transient Thermal Impedance

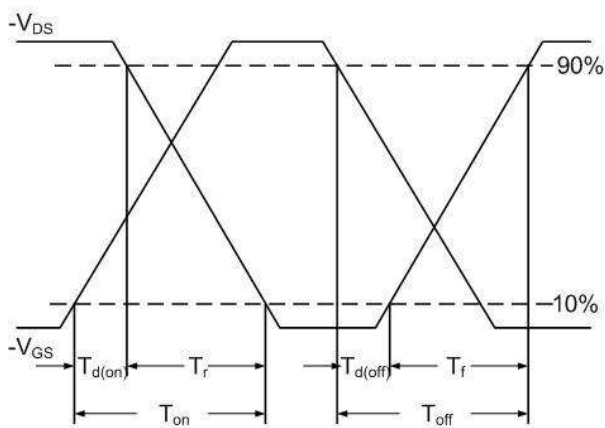


Fig.10 Switching Time Waveform

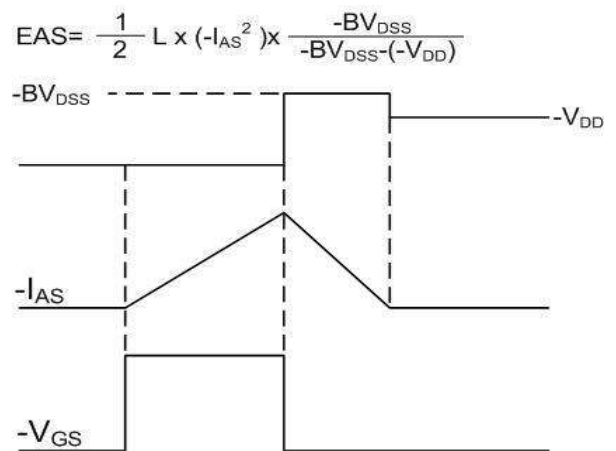
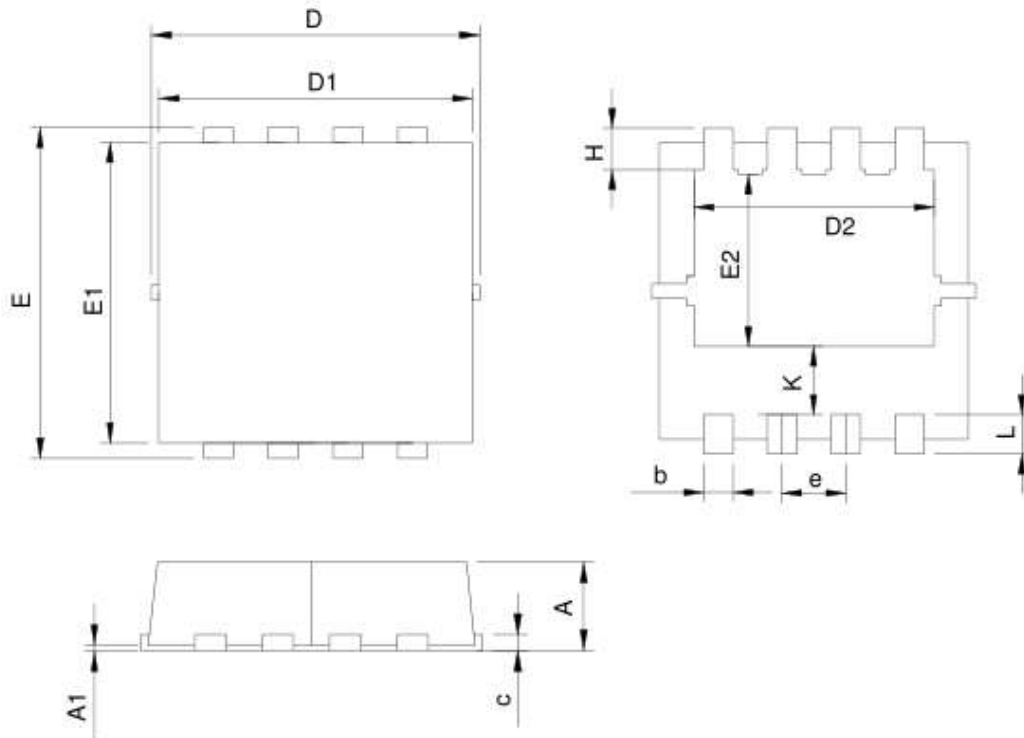


Fig.11 Unclamped Inductive Waveform

AP18P10Q

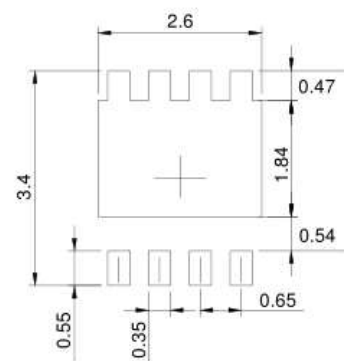
P-Channel Enhancement Mosfet

PDFN3X3-8L Package Information



Symbol	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm